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AS

1. A semiconductor integrated circuit device having a first MIS transistor of a first conductivity type, a second MIS transistor of a second conductivity type, and a resistor connected in series between a first power-source line and a second power-source line, comprising:

a third MIS transistor of the first conductivity type having a gate connected to a node where said first MIS transistor and said second MIS transistor are connected together, and a drain connected to a connection node where said second MIS transistor and said resistor are connected together.

2. The semiconductor integrated circuit device as claimed in claim 1, further comprising:

fourth and fifth MIS transistors of the second conductivity type current mirror-connected to said second MIS transistor;

a sixth MIS transistor of the first conductivity type connected between said fourth transistor and to said first power-source line, and is current mirror-connected to said first MIS transistor; and

a seventh MIS transistor of the first conductivity type connected between said fifth MIS transistor and to said first power-source line, and a gate of said seventh MIS transistor being connected to a node where said first MIS transistor and said second MIS transistor are connected together.

3. The semiconductor integrated circuit device as claimed in claim 1, further comprising:

an eighth MIS transistor of the first conductivity type having a source connected to said first power-source line, and a gate connected to a node where said first MIS transistor and second MIS transistor are connected together, in order to produce an output current.

4. The semiconductor integrated circuit device as claimed in claim 1, further comprising:

a ninth MIS transistor of the second conductivity type connected between said second MIS transistor and said resistor; and

tenth and eleventh MIS transistors of the second conductivity type connected between said second power-source line and said fourth and fifth MIS transistors, wherein said ninth, tenth and eleventh MIS transistors are connected to said second, fourth and fifth MIS transistors in cascade.

5. The semiconductor integrated circuit device as claimed in claim 1, wherein said first MIS transistor has characteristics different from those of other MIS transistors of the first conductivity type.

6. The semiconductor integrated circuit device as claimed in claim 5, wherein said first MIS transistor having different characteristics is of a size smaller than those of said other MIS transistors of the first conductivity type.

7. The semiconductor integrated circuit device as claimed in claim 5, wherein said first MIS transistor having different characteristics is of a threshold voltage higher than those of said other MIS transistors of the first conductivity type.

8. The semiconductor integrated circuit device as claimed in claim 5, wherein said first MIS transistor having different characteristics gives a substrate bias larger than those of said other MIS transistors of the first conductivity type.

CLAIMS 9-27 (CANCELLED)